

FAST RECOVERY DIODES

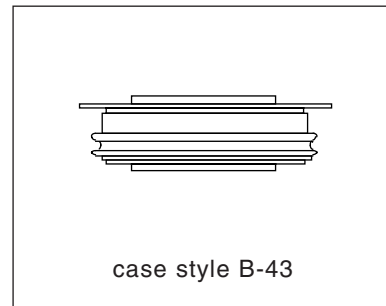
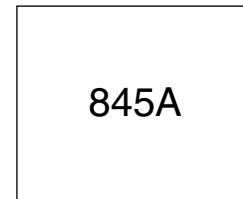
Hockey Puk Version

Features

- High power FAST recovery diode series
- 1.0 to 1.5 μ s recovery time
- High voltage ratings up to 1600V
- High current capability
- Optimized turn on and turn off characteristics
- Low forward recovery
- Fast and soft reverse recovery
- Press-puk encapsulation
- Case style conform to JEDEC B-43
- Maximum junction temperature 125°C

Typical Applications

- Snubber diode for GTO
- High voltage free-wheeling diode
- Fast recovery rectifier applications



Major Ratings and Characteristics

Parameters	SD803C..C	Units
$I_{F(AV)}$	845	A
@ T_{hs}	55	°C
$I_{F(RMS)}$	1326	A
@ T_{hs}	25	°C
I_{FSM}	@ 50Hz 11295	A
	@ 60Hz 11830	A
I^2t	@ 50Hz 640	KA ² s
	@ 60Hz 583	KA ² s
V_{RRM} range	400 to 1600	V
t_{rr} range	1.0 to 1.5	μ s
@ T_J	25	°C
T_J	- 40 to 125	°C

SD803C..C Series

Bulletin I2069 rev.B 04/00

International
IR Rectifier

ELECTRICAL SPECIFICATIONS

Voltage Ratings

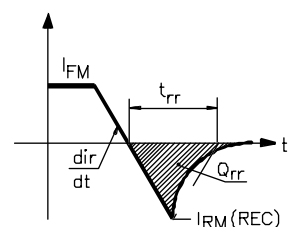
Type number	Voltage Code	V _{RRM} max. repetitive peak and off-state voltage V	V _{RSM} , maximum non-repetitive peak voltage V	I _{RRM} max. T _J = 125°C mA
SD803C..S10C	04	400	500	45
	08	800	900	
	10	1000	1100	
SD803C..S15C	12	1200	1300	
	14	1400	1500	
	16	1600	1700	

Forward Conduction

Parameter	SD803C..C	Units	Conditions
I _{F(AV)} Max. average forward current @ Heatsink temperature	845(420)	A	180° conduction, half sine wave.
	55(75)	°C	Double side (single side) cooled
I _{F(RMS)} Max. RMS current	1326	A	@ 25°C heatsink temperature double side cooled
I _{FSM} Max. peak, one-cycle non-repetitive forward current	11295	A	t = 10ms No voltage
	11830		t = 8.3ms reapplied
	9500		t = 10ms 100% V _{RRM}
	9945		t = 8.3ms reapplied
I ² t Maximum I ² t for fusing	640	KA ² s	t = 10ms No voltage
	583		t = 8.3ms reapplied
	451		t = 10ms 100% V _{RRM}
	412		t = 8.3ms reapplied
I ² /t Maximum I ² /t for fusing	6400	KA ² /s	t = 0.1 to 10ms, no voltage reapplied
V _{F(TO)1} Low level of threshold voltage	1.02	V	(16.7% × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J max.
V _{F(TO)2} High level of threshold voltage	1.32		(I > π × I _{F(AV)}), T _J = T _J max.
r _{f1} Low level of forward slope resistance	0.38	mΩ	(16.7% × π × I _{F(AV)} < I < π × I _{F(AV)}), T _J = T _J max.
r _{f2} High level of forward slope resistance	0.28		(I > π × I _{F(AV)}), T _J = T _J max.
V _{FM} Max. forward voltage	1.89	V	I _{pk} = 2655A, T _J = 25°C, t _p = 10ms sinusoidal wave

Recovery Characteristics

Code	T _J = 25°C typical t _{rr} @ 25% I _{RRM} (μs)	Test conditions			Max. values @ T _J = 125°C		
		I _{pk} Square Pulse (A)	di/dt (A/μs)	V _r (V)	t _{rr} @ 25% I _{RRM} (μs)	Q _{rr} (μC)	I _{rr} (A)
S10	1.0	1000	25	-30	2.0	45	34
S15	1.5				3.2	87	51



Thermal and Mechanical Specifications

Parameter	SD803C..C	Units	Conditions
T _J Max. operating temperature range	-40 to 125	°C	
T _{stg} Max. storage temperature range	-40 to 150		
R _{thJ-hs} Max. thermal resistance, junction to heatsink	0.076 0.038	K/W	DC operationsingle side cooled DC operationdouble side cooled
F Mounting force, ± 10%	9800 (1000)		N (Kg)
wt Approximate weight	83	g	
Case style	B-43		See Outline Table

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.006	0.007	0.005	0.005	K/W	T _J = T _J max.
120°	0.008	0.008	0.008	0.008		
90°	0.010	0.010	0.011	0.011		
60°	0.015	0.015	0.016	0.016		
30°	0.026	0.026	0.026	0.026		

Ordering Information Table

Device Code

SD	80	3	C	16	S15	C
①	②	③	④	⑤	⑥	⑦

- 1** - Diode
- 2** - Essential part number
- 3** - 3 = Fast recovery
- 4** - C = Ceramic Puk
- 5** - Voltage code: Code x 100 = V_{RRM} (see Voltage Ratings table)
- 6** - t_{rr} code (see Recovery Characteristics table)
- 7** - C = Puk Case B-43

SD803C..C Series

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Outline Table

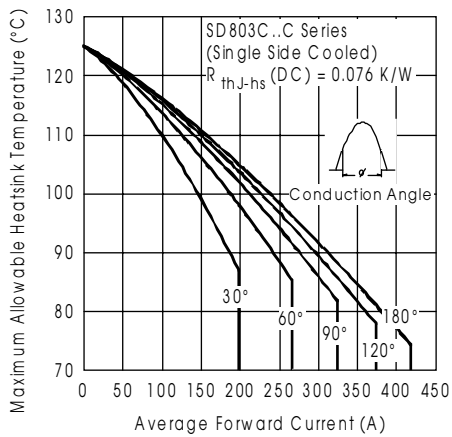
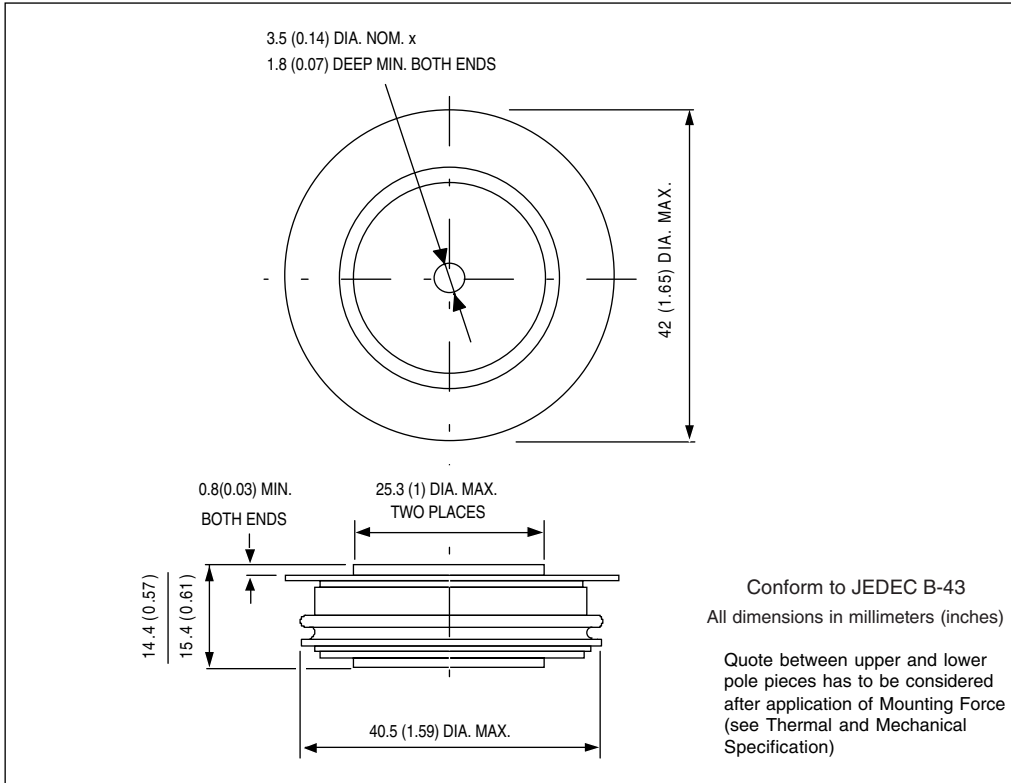


Fig. 1 - Current Ratings Characteristics

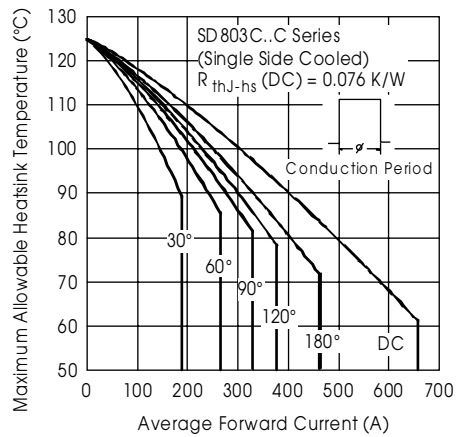


Fig. 2 - Current Ratings Characteristics

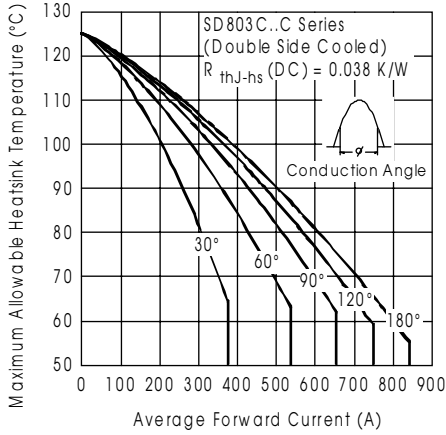


Fig. 3 - Current Ratings Characteristics

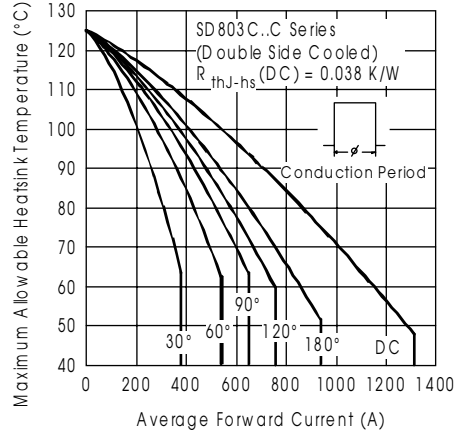


Fig. 4 - Current Ratings Characteristics

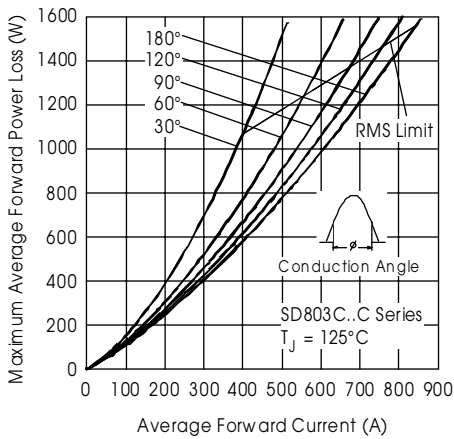


Fig. 5 - Forward Power Loss Characteristics

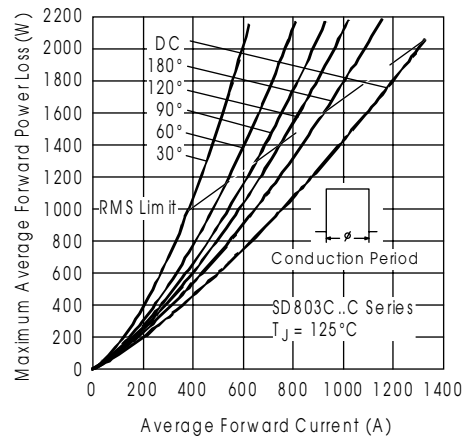


Fig. 6 - Forward Power Loss Characteristics

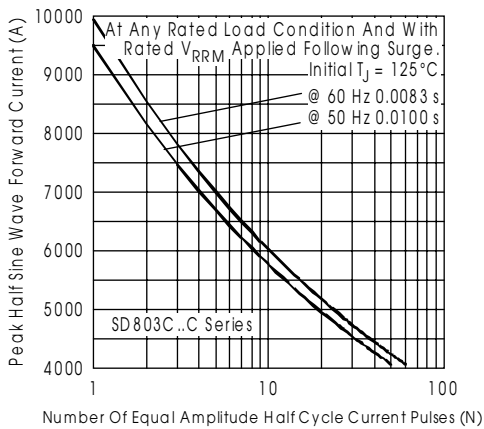


Fig. 7 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

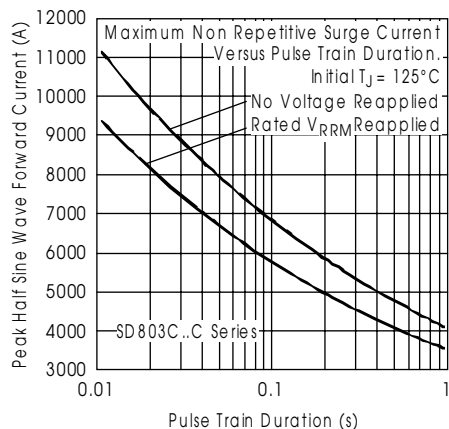


Fig. 8 - Maximum Non-repetitive Surge Current Single and Double Side Cooled

SD803C..C Series

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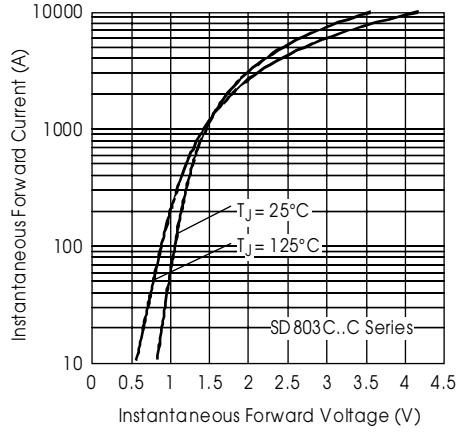


Fig. 9 - Forward Voltage Drop Characteristics

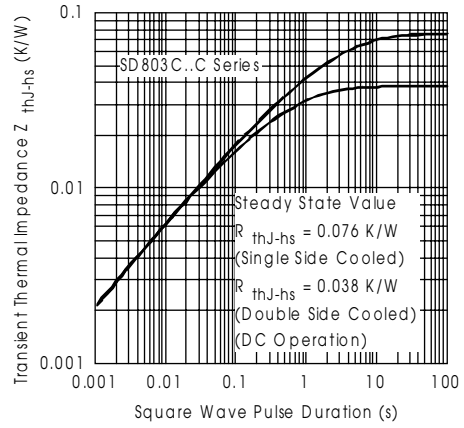


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristic

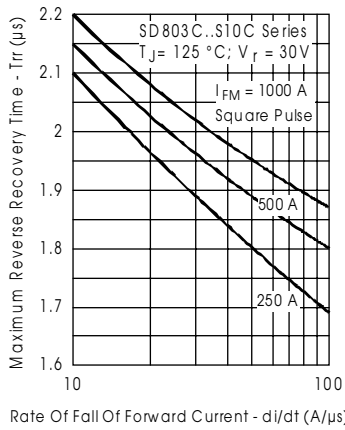


Fig. 11 - Recovery Time Characteristics

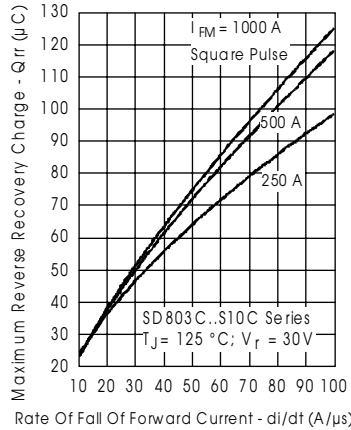


Fig. 12 - Recovery Charge Characteristics

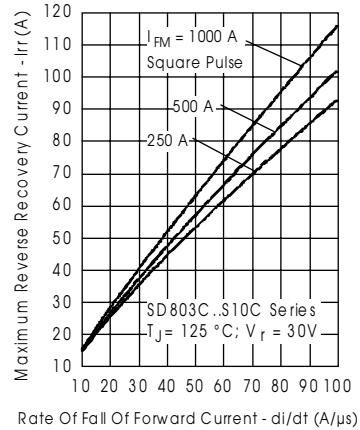


Fig. 13 - Recovery Current Characteristics

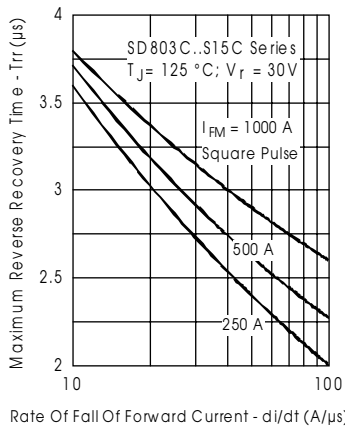


Fig. 14 - Recovery Time Characteristics

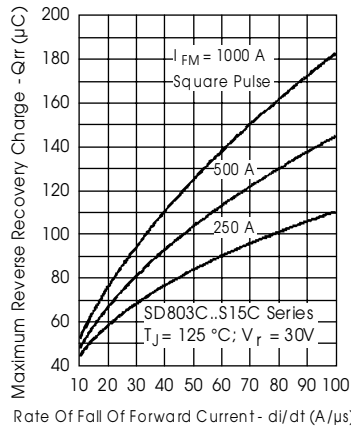


Fig. 15 - Recovery Charge Characteristics

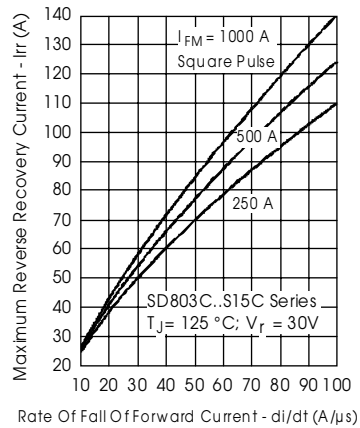


Fig. 16 - Recovery Current Characteristics

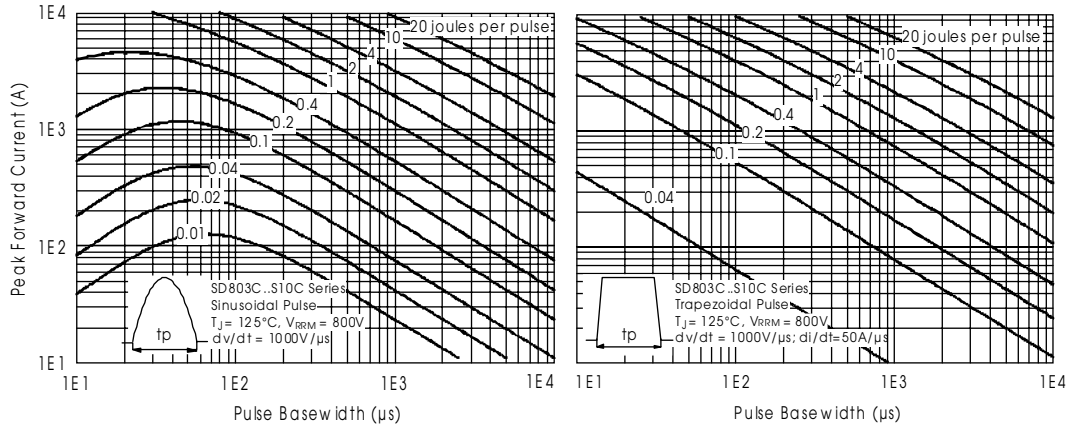


Fig. 17 - Maximum Total Energy Loss Per Pulse Characteristics

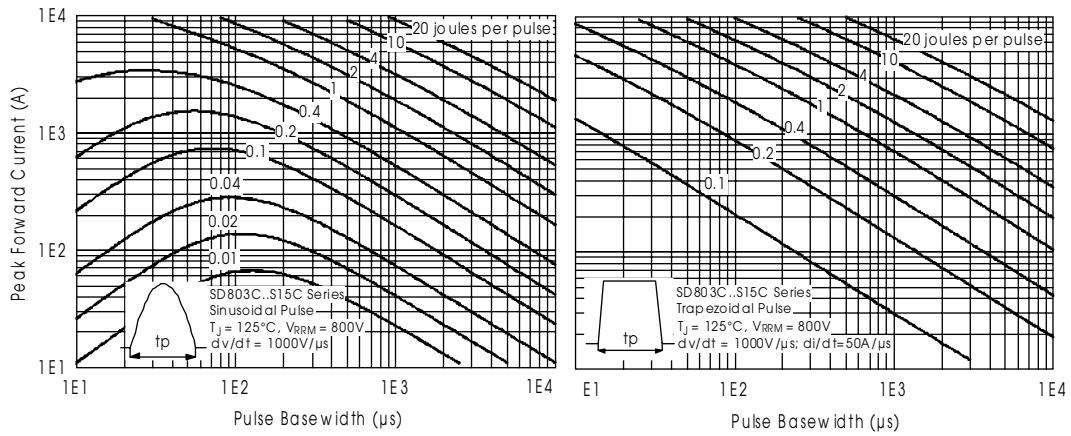


Fig. 18 - Maximum Total Energy Loss Per Pulse Characteristics